

REMARKS

Applicant thanks the Examiner for recognizing that claims 7-18 and 21-27 include allowable subject matter. Claims 5 and 21, however, remain rejected as anticipated by U.S. Patent No. 5,578,514 (Kwon et al.).

In connection with the Kwon et al. patent, the Office action alleges that the drift region 24 (FIG. 2), which is produced as the result of a drive-in process, inherently results in regions of different impurity concentrations and, therefore, corresponds to the first and second drain regions recited in pending claim 5.

Claim 5 has been amended to clarify that the implant step includes implanting an impurity of a first conductive type in “first and second drain formation regions” of a semiconductor substrate, wherein the first drain region is formed in the first drain formation region and the second drain region is formed in the second drain region. As shown, for example, in FIG. 4 of the pending application, ions are implanted in both the first drain formation region (where the first drain region 5A is formed) and the second drain formation region (where the second drain region 5B is formed).

In contrast, according to the Kwon et al. patent, dopant 22 is implanted in a implant area 22. Even if the drift region 24 formed by the subsequent drive-in process (FIG. 2) were considered to result in the formation of regions having different impurity concentrations, the implant is provided only in the implant area 22, not the entire drift region 24. Therefore, Kwon et al. does not disclose implanting in both first and second drain formation regions, as recited in claim 5.

At least for those reasons, claim 5 (as amended), as well as dependent claim 21, should be allowed.

Nor does the Kwon et al. patent disclose the additional feature(s) of claim 29, which recites that the first and second drain formation regions into which the impurity is implanted have different impurity concentrations. As is clear from FIG. 1 of the Kwon et al. patent, the

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entire implant area 22 into which the dopant 23 is implanted has the same concentration. At least for that additional reason, claim 29 should be allowed.

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Respectfully submitted,

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